

GENERAL STUDIES & ENGINEERING APTITUDE

PRACTICE QUESTIONS BOOK

*UPSC Engineering Services
Preliminary Examinations Paper-I*



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Fifth Edition :- 2024

Preface

Engineering Services Exam (ESE) is one of most coveted exams written by engineering students aspiring for reputed posts in the country. As all the senior engineering posts come under the Government of India, ESE is conducted by the Union Public Services Commission (UPSC), and therefore the standards to clear this exam too are very high. To clear the ESE, a candidate needs to clear three stages – ESE Prelims, ESE Mains and Personality Test.

This revised and updated self-practice question book is an endeavour by IES Master to help ESE aspirants clear the Paper-1 i.e. General Studies & Engineering Aptitude of the very first stage i.e. ESE Prelims. The Paper-1 carries 200 marks, and should not be taken lightly. With more than 3,400 practice questions sorted subject-wise, students will get a chance to quickly brush through all the subjects in a short span. Practising as many questions possible will help candidates in going through whatever they have learned so far, and will count as a round of revision. The detailed solution to each question will help them identify their strengths and weaknesses, and build confidence before taking the real ESE Prelims. The detailed solutions to questions will also help candidates in understanding the appropriate methods in answering a question and improve their speed and accuracy.

IES Master feels immense pride in bringing out this new edition of practice book as every care has been taken to build upon the exam preparedness of a student right up to UPSC standards. The credit for flawless preparing of this book for ESE aspirants goes to the entire team of IES Master Publications. Teachers, students, and professional engineers are welcome to share their suggestions to make this book more valuable.

**IES Master Publication
New Delhi**

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Basics of Material Science & Engineering

1. Which of the following statement(s) is/are correct regarding ionic bond.
- (a) These are directional in nature
 - (b) These are non-directional in nature
 - (c) These are not brittle
 - (d) These are ductile
2. Which of the statement is/are correct regarding electron affinity of the atom
- I. Inert gases has no affinity for an extra electron
 - II. Halogens are just one electron short to achieve the stable inert gas configuration
 - III. When extra e^- added to a neutral atom, there is a weakening of the repulsion of electrons to the nucleus.
- (a) I, II
 - (b) I, III
 - (c) II, III
 - (d) All
3. Which of the following statement is/are correct
- Statement (I)** : Ionic bonds are strongest bond while metallic bonds are weakest bond among the primary bond
- Statement (II)** : In metals, atom move from one position to another without breaking of the bonds
- (a) I
 - (b) II
 - (c) Both
 - (d) None
4. Which of the following statement is/are correct regarding to paramagnetic material.
- I. Magnetic susceptibility of these material is small but positive.
 - II. Magnetic susceptibility of these material is higher and greater than ferromagnetic.
 - III. Increase in temperature of material, randomness of dipole increase.
 - IV. Randomness in dipole independent of temperature.
- (a) I, III
 - (b) I, V
 - (c) II, III
 - (d) II, IV
5. Which of the following statement is/are correct
- Statement I** : Ferromagnetic material shows spontaneous magnetization.
- Statement II** : Diamagnetic materials are repelled from applied magnetic field
- (a) I
 - (b) II
 - (c) Both I & II
 - (d) Neither I nor II
6. The materials with permeability less than unity are called
- (a) Diamagnetic materials
 - (b) Paramagnetic materials
 - (c) Ferromagnetic materials
 - (d) Anti ferromagnetic material
7. Retentivity is/are
- I. Maximum value of residual magnetization
 - II. Minimum value of permanent magnetization
 - III. Maximum value of spontaneous magnetization
 - IV. Maximum value which a coercive field can attain
- (a) I, II, IV
 - (b) I, III
 - (c) III, IV
 - (d) II, III
8. Which of the statement is/are correct regarding antiferro magnetic material.
- I. Magnetic susceptibility for these material is small but $-ve$
 - II. Magnetic susceptibility for these material is small but $+ve$
 - III. Above Neels temperature they behave as paramagnetic material
 - IV. Above Neels temperature they behave as diamagnetic material.
- (a) I, III
 - (b) I, IV
 - (c) II, III
 - (d) II, IV

Statement I : Frenkel's defect occurs when cations are displaced into the interstitial space formed between anions.

Statement II : Over all electrical neutrality of the ionic crystal is maintained in Frenkel's defect but disturbed in Schottky's defect.

Statement III : Schottky's defect is mainly interstitial type point defect.

- (a) I (b) II, III
(c) I, II (d) All
- 21.** Consider the following statements with regard to BCC structure.
1. Number of nearest neighbour atoms is six
 2. Packing efficiency is .68
 3. There is an atom at the body centre of the unit cell
- (a) 1, 2 (b) 2, 3
(c) 1, 3 (d) All
- 22.** A solid in which all similar atoms are in similar position relative to their neighbours is said to
- I. have long-range order
 - II. be crystalline
 - III. be amorphous
- (a) I (b) II
(c) I, II (d) All
- 23.** Which of the following are closed packed structures
- I. h.c.p.
 - II. tetragonal
 - III. bcc
 - IV. FCC
- (a) I, II (b) II, III
(c) III, IV (d) I, IV
- 24.** A polymorphic material is one that
- I. is found naturally in many different shapes
 - II. has more than one kind of crystal structure
 - III. displays allotropic forms
- (a) I, II (b) II, III
(c) I, III (d) All
- 25.** In defining Miller Indices we set up coordinate axes
- I. along the edge of the unit cell
 - II. along the (100) directions
 - III. perpendicular to the faces of the unit cell
- (a) I (b) II, III
(c) III (d) I, III
- 26.** The (110) direction in a unit cell is parallel to
- I. the diagonal of one face of the cell
 - II. the body diagonal of the cell
 - III. one edge of the cube
- (a) I (b) I, II
(c) II (d) III
- 27.** Which of the following statement is/are correct regarding intrinsic semiconductors
- I. at room temperature intrinsic semi conductors shows conductivity
 - II. electron and hole both moves in conduction band from valance band
- (a) I (b) II
(c) Both I and II (d) Neither I nor II
- 28.** Which of the statement is correct
- I. Mobility of electron is always greater than mobility of hole
 - II. at room temperature intrinsic carrier concentration (n_i) in Ge is greater than Si
- (a) I (b) II
(c) Both (d) None
- 29.** Which of the following statement is/are correct regarding extrinsic semi conductors.
- I. For n-type semiconductors pentavalent impurity is added
 - II. For p-type semiconductors IIIrd group impurity is added
 - III. N-type semiconductors are over all electrically neutral.
- (a) I, II (b) II, III
(c) III, I (d) All
- 30.** Which statement is/are correct
- I. For n-type semiconductor majority charge carrier concentration proportional to donor concentration.
 - II. For p-type semiconductor, conductivity is proportional to acceptor concentration
- (a) I (b) II
(c) Both (d) None
- 31.** Which of statement is correct regarding to valance band
- I. It is the highest band in which electron are still associated with their parent atom
 - II. V.B. electron used thermal energy to free themselves from grip of their parent atom
 - III. V.B. electron are responsible for current flow.
- (a) I, II (b) II, III
(c) I, III (d) All

42. The elastic strain obtained on applying a stress to a material is
 I. time-dependent
 II. instantaneous
 III. reversible
 IV. directly proportional to the stress
 V. inversely proportional to the stress
 (a) I, II, III, IV (b) II, III, IV
 (c) II, III, V (d) I, II, III
43. If poisson's ratio during elastic deformation under uniaxial tensile stress is less than 0.5
 I. there is a contraction in each of the two lateral direction
 II. There is a expansion in each of the two lateral directions
 III. There is a decrease in specimen volume
 IV. There is an increase in specimen volume
 (a) I, III (b) I, IV
 (c) II, III (d) II, IV
44. The elastic resilience of a material is
 I. the stored energy per unit volume during elastic deformation
 II. the stored energy per unit volume associated with dislocations
 III. given by $\frac{1}{2} \epsilon^2 E$
 IV. given by $\frac{1}{2} \sigma \epsilon$
 (a) I, II, IV (b) I, III, IV
 (c) I, III (d) II, III, IV
45. The true strain is given by
 I. $\ln\left(\frac{\ell_1}{\ell_0}\right)$ II. $\frac{\Delta \ell}{\ell_0}$
 III. $\frac{l}{l_0}$ IV. $\ln(1+e)$
 (a) I, III (b) II, III
 (c) I, IV (d) III, IV
46. The Application of Hall effect is/are
 I. To determine the carrier concentration
 II. To determine whether the specimen is metal or semiconductor
 III. To calculate the mobility of carriers
 (a) I, II (b) II, III
 (c) I, III (d) all
47. Find out correct statement/statements regarding to hall effect.
Statement I: Hall coefficient for metal is zero.
Statement II: Hall voltage for metals are in the range of micro meter while for the n-type semiconductor it is in the range of millimeter.
 (a) I (b) II
 (c) both (d) neither I nor II
48. Basic constituents of engineering ceramics are
 I. alumina II. silicon carbide
 III. silicon nitrite IV. silicon phosphite
 (a) I, II, III (b) II, III, IV
 (c) I, III, IV (d) all
49. Which of the following is/are correct related to ceramic materials
 I. crystal structure of ceramic is influenced by the magnitude of electrical charge on each of the component ions.
 II. stable ceramic crystal structure is formed when all the anion surrounding the cation are in direct contact with that cation.
 (a) I (b) II
 (c) both (d) none
50. Which of the following statement is/are correct related to rock salt structure.
 I. Co-ordination for both cation and anion is '6'
 II. Radius ratio varies from $.414 < \frac{r_C}{r_A} < .732$
 (a) I (b) II
 (c) both (d) none
51. Which of the following is/are correct regarding ceramics?
 I. Ceramics have high value of dielectric constant.
 II. Ceramics materials have high value of corrosion resistance
 III. Ceramics are ductile in nature
 (a) I, III (b) I, II
 (c) II, III (d) I, II, III
52. Vitrification is
 I. The transformation from a glassy to a crystalline state
 II. The densification in the presence of a viscous liquid
 III. Important during the firing of clays

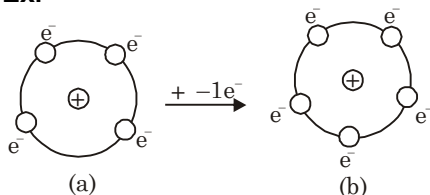
- I. It consist of 12 hexagonal and 20 pentagonal structure.
 II. It consist of 20 hexagonal and 12 pentagonal structure.
 III. No two hexagon share a common side.
 IV. No two pentagon share a common side.
 (a) I, III (b) I, IV
 (c) II, III (d) II, IV
- 64.** Which of the following statement is/are correct regarding sintering?
 I. This thermal treatment in ceramic manufacturing result in the transformation of porous compact into a dense.
 II. Particles are coalesced by solid state diffusion.
 III. Temperature is always less than melting point, throughout the process.
 (a) I, II (b) II, III
 (c) III, I (d) all
- 65.** Which of the following statement is/are correct regarding sintering?
 I. Thermoplastic are more temperature sensitive than thermo setting polymer.
 II. Thermoplastic are formed by polymerization where as thermo settings are formed by condensation polymerization.
 (a) I (b) II
 (c) both (d) none
- 66.** In pack carburising, energizer used is :
 (a) 5%CaCO₃ (b) 5%Na₂CO₃
 (c) 20%CaCO₃ (d) 20%Ba₂CO₃
- 67.** Vulcanisation is/are
 I. It is a cross linking process in elastomers.
 II. Sulphur compounds are added.
 III. Decrease the modulus of elasticity of rubber.
 (a) I, II (b) II, III
 (c) I, III (d) all
- 68.** Which of the following statement is/are correct regarding polymer additions?
 I. Filler materials are added to polymer to improve tensile and compressive strength, abrasion resistance, toughness etc.
 II. Plasticizers provide flexibility, ductility and toughness to polymers.
 III. Plasticizers improve hardness and toughness of polymers.
 (a) I, II (b) II, III
 (c) I, III (d) all
- 69.** Plasticizers
 I. improve flexibility II. improve toughness
 III. improve stiffness IV. decrease hardness
 (a) I, II, III (b) I, II, IV
 (c) I, III, IV (d) all
- 70.** Thermoplastic material is/are
 I. PVC II. Teflon
 III. Polystyrene IV. Polyester
 (a) I, II, III (b) I, II, IV
 (c) II, III, IV (d) all
- 71.** Which of the following are characteristic of plastics?
 I. Low density II. Machinability
 III. High strength
 IV. Large plastic deformation
 (a) I, II, III (b) I, II, IV
 (c) II, III, IV (d) all
- 72.** In a thermoplastic polymer, adjacent molecules are bonded by
 I. primary bonds
 II. secondary bonds
 III. covalent bonds
 IV. vander waals or hydrogen bonds
 (a) I, III (b) II, III, IV
 (c) II, IV (d) I, III, IV
- 73.** In a thermoplastic polymer, side groups are bonded to the backbone by
 I. primary bonds
 II. secondary bonds
 III. covalent bonds
 IV. vander waals or hydrogen bonds
 (a) I, III (b) II, IV
 (c) I, III, IV (d) I, II, III
- 74.** Thermosetting polymers is/are
 I. consist of a network of polymer chains
 II. can not be remoulded
 III. are generally more rigid than thermoplastic polymer
 IV. have very temperature sensitive mechanical

SOLUTION...

1. (b) Atom moment within the crystal is not possible without breaking the bond which makes there material characteristically non directional i.e., in ionic compounds there is no intrinsically preferred direction in which a neighbour should lie for the strength of bonding to be maximum.

2. (a)
- ⇒ Inert gases have completed their octet so they are stable and has no affinity for an extra e^-
 - ⇒ Halogens are required e^- to complete their octate so that can achieve inert gas configuration
 - ⇒ When extra e^- added to a neutral atom, there is an increase in the repulsion b/w the e^- 's.

Ex.



From figure clearly seen that state 'a' have $4e^-$ which have less repulsion than state 'b' which have $5e^-$

3. (c) Due to high electrostatic attraction b/w atoms ionic bonds are strongest bond in among the primary bond.
- ⇒ Statement II is correct.

4. (a) On the application of magnetic field we get a small value of magnetization in the field direction hence for these material magnetic susceptibility small but positive

⇒ $\uparrow T$ randomness \uparrow

5. (c)
- ⇒ Ferromagnetic material get magnetised in the direction of applied magnetic field and remain magnetised even after removal of field. This property of ferro megnetic material is called spontaneous magnetisation

⇒ Dia magnetic materials are repelled from applied magnetic field because magnetic susceptibility is '-ve'.

6. (a) For diamagnetic materials $\chi_m < 0$

$$\mu_r - 1 < 0$$

$$\boxed{\mu_r < 1}$$

7. (b) Retentivity is the maximum value of residual permanent/spontaneous magnetization.

8. (c) Anti-ferromagnetic material are charecterised by anti parallel arrangement of dipole so net magnetization is zero, even in the presence of an applied filed these material have small positive suceptibility at all the temperature.

⇒ They remain antiferro magnetic upto Neel's temp. and above Neel's temperature they behave like paramagnetic materials.

9. (b) Ferrite have more resitivity than ferro magnetic material so eddy losses are less in ferrite also, ferrites have DC resistivity of many orders of ten higher than in iron, and are used for frequencies upto microwave in transformer.

Above curie temperature thermal agitation is so great that internal field is not sufficient to maintain alignment of magnetic dipole.

10. (c)
- ∴ Diamagnetic material has negative magnetic susceptivityso they repelled by magnetic field because of this they moves from stronger magnetic field to weaker magnetic field.

∴ Diamagnetic material reduces the applied magnetic field so these permeability is less than free space permeability i.e., $\boxed{\mu < \mu_0}$.

11. (a) Magnetostriction : Is a property of ferro-magnetic materials that cause them to change their shape or dimensions during the process of magnetization.

12. (c) The magnetostriction characterizes the shape change of a ferro magnetic material during magnetization, where as the inverse magnetostrictive effect charecterizes the change of sample magnetization when mechanical stresses σ are applied to the sample.